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TiN/Hf$_x$Zr$_{1-x}$O$_2$/TiN 铁电电容器的原位生长与表征

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In Situ Growth and Characterization of TiN/Hf$_x$Zr$_{1-x}$O$_2$/TiN Ferroelectric Capacitors

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S1 Calculation of ZrO_2 content of $Hf_xZr_{1-x}O_2$ film with ALD pulsing ratio of 1 : 1.

Table S1 Calculation of ZrO_2 content.

Heading 1	Peak Area	RSF	Content
Hf	49840	211.335	49.72%
Zr	52187	223.768	50.28%

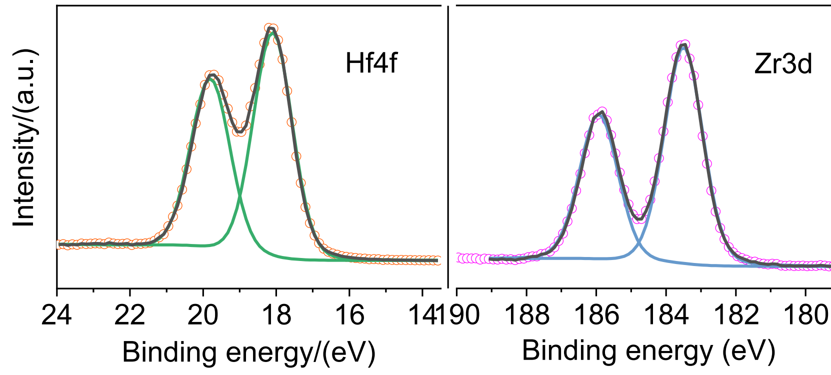

Fig. S1 Hf 4*f* (left) and Zr 3*d* (right) XPS spectra of $Hf_xZr_{1-x}O_2$ film with ALD pulsing ratio of 1 : 1.